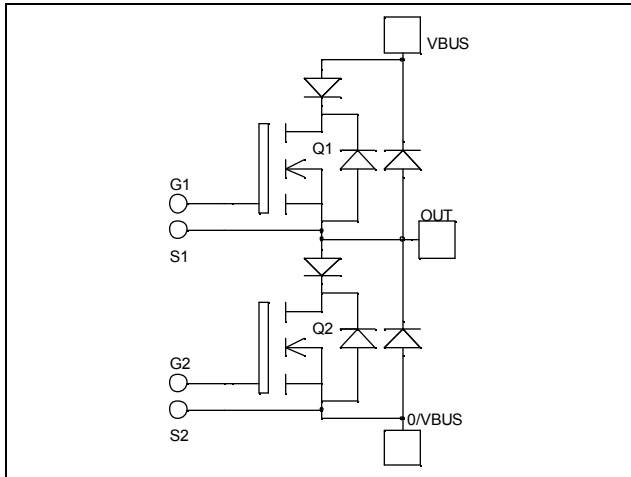


*Phase leg
Series & parallel diodes
MOSFET Power Module*

$$V_{DSS} = 1000V$$

$$R_{DSon} = 130m\Omega \text{ typ @ } T_j = 25^\circ C$$

$$I_D = 65A \text{ @ } T_c = 25^\circ C$$

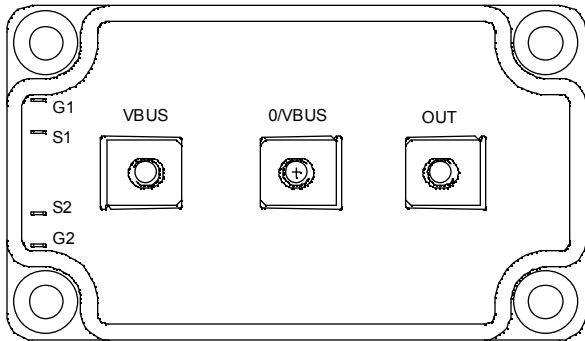


Application

- Motor control
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration




Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1000	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	65
		$T_c = 80^\circ C$	49
I_{DM}	Pulsed Drain current	240	A
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	156	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	1250
I_{AR}	Avalanche current (repetitive and non repetitive)	24	A
E_{AR}	Repetitive Avalanche Energy	30	mJ
E_{AS}	Single Pulse Avalanche Energy	1300	

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{V}, V_{DS} = 1000\text{V}$			600	μA
		$V_{GS} = 0\text{V}, V_{DS} = 800\text{V}$			2	mA
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 32.5\text{A}$		130	156	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 6\text{mA}$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$			± 450	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$		15.2		nF
C_{oss}	Output Capacitance	$V_{DS} = 25\text{V}$		2.6		
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.42		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$		562		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 500\text{V}$		75		
Q_{gd}	Gate – Drain Charge	$I_D = 65\text{A}$		363		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C		9		ns
T_r	Rise Time	$V_{GS} = 15\text{V}$		9		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 667\text{V}$		50		
T_f	Fall Time	$I_D = 65\text{A}$ $R_G = 0.5\Omega$		24		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C		2.13		mJ
E_{off}	Turn-off Switching Energy	$V_{GS} = 15\text{V}, V_{Bus} = 667\text{V}$ $I_D = 65\text{A}, R_G = 0.5\Omega$		0.46		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C		4.4		mJ
E_{off}	Turn-off Switching Energy	$V_{GS} = 15\text{V}, V_{Bus} = 667\text{V}$ $I_D = 65\text{A}, R_G = 0.5\Omega$		0.57		

Series diode ratings and characteristics

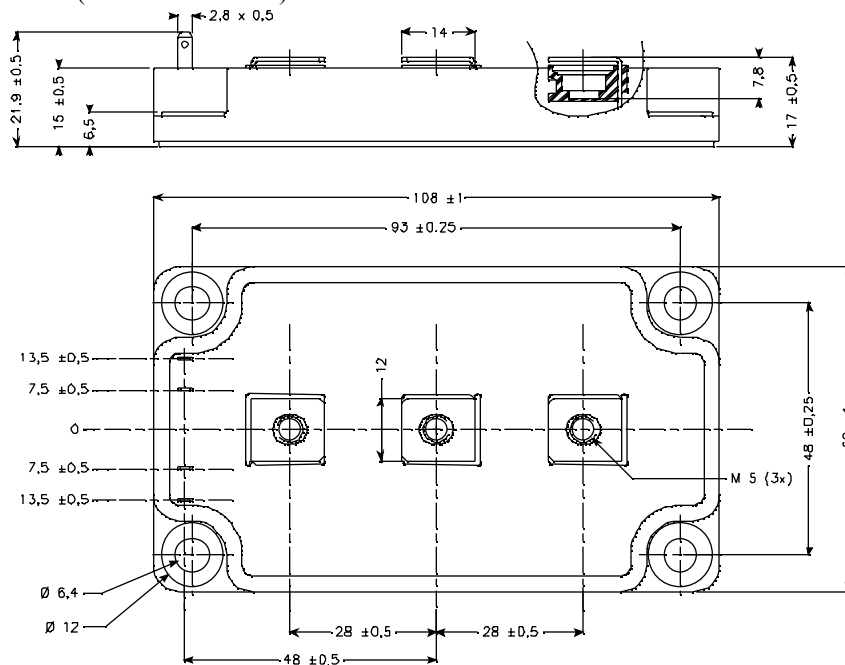
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Repetitive Reverse Voltage		200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 200\text{V}$	$T_j = 25^\circ\text{C}$		350	μA
			$T_j = 125^\circ\text{C}$		600	
I_F	DC Forward Current			60		A
V_F	Diode Forward Voltage	$I_F = 60\text{A}$		1.1	1.15	V
		$I_F = 120\text{A}$		1.4		
		$I_F = 60\text{A}$	$T_j = 125^\circ\text{C}$	0.9		
t_{rr}	Reverse Recovery Time	$I_F = 60\text{A}$ $V_R = 133\text{V}$	$T_j = 25^\circ\text{C}$	24		ns
			$T_j = 125^\circ\text{C}$	48		
Q_{rr}	Reverse Recovery Charge	$di/dt = 400\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	66		nC
			$T_j = 125^\circ\text{C}$	300		

Parallel diode ratings and characteristics

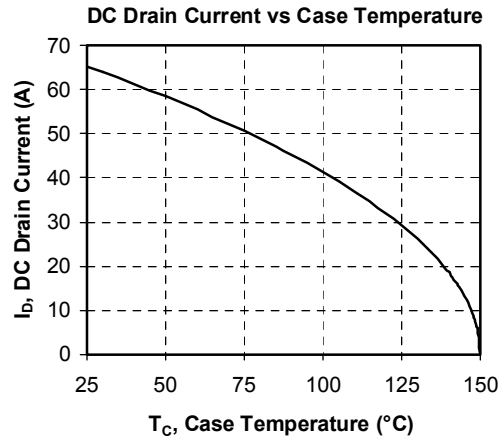
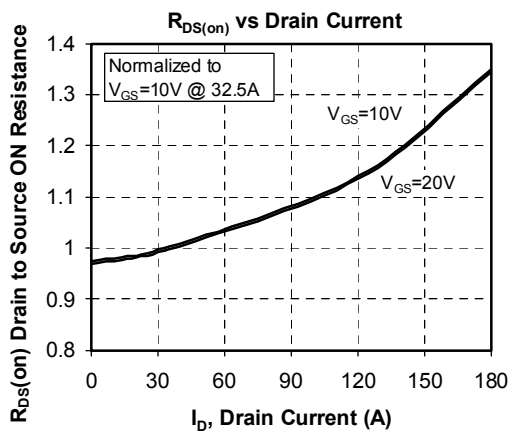
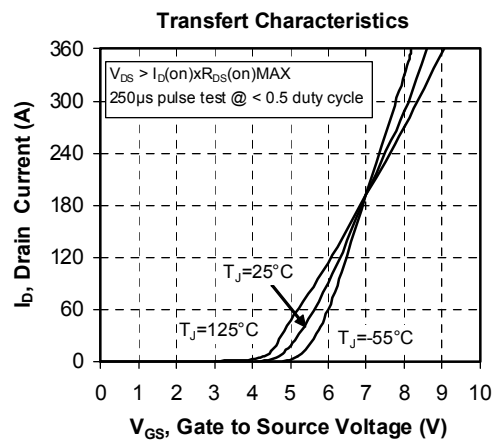
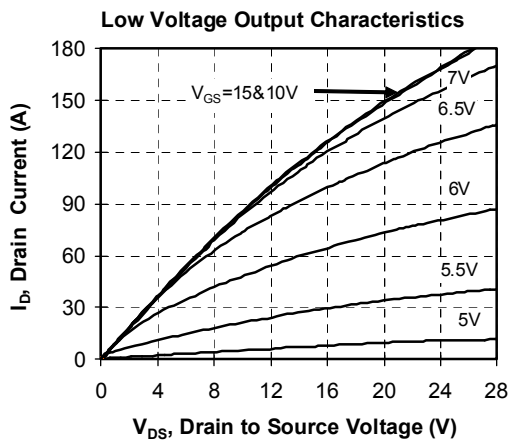
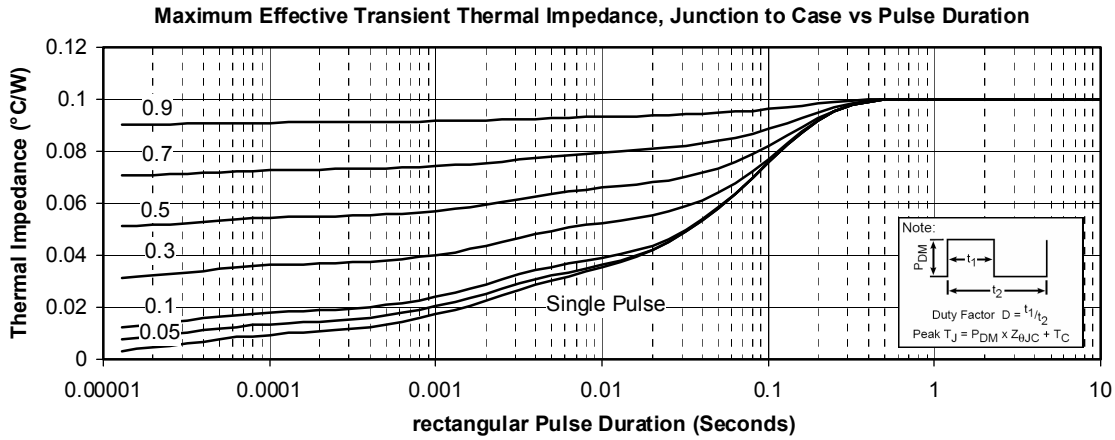
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Repetitive Reverse Voltage		1000			V
I_{RM}	Maximum Reverse Leakage Current	$V_R=1000V$	$T_j = 25^\circ C$		350	μA
			$T_j = 125^\circ C$		600	
I_F	DC Forward Current			120		A
V_F	Diode Forward Voltage	$I_F = 120A$		1.9	2.5	V
		$I_F = 240A$		2.2		
		$I_F = 120A$	$T_j = 125^\circ C$	1.7		
t_{rr}	Reverse Recovery Time	$I_F = 120A$ $V_R = 667V$	$T_j = 25^\circ C$	280		ns
			$T_j = 125^\circ C$	350		
Q_{rr}	Reverse Recovery Charge	$di/dt = 400A/\mu s$	$T_j = 25^\circ C$	1520		nC
			$T_j = 125^\circ C$	7200		

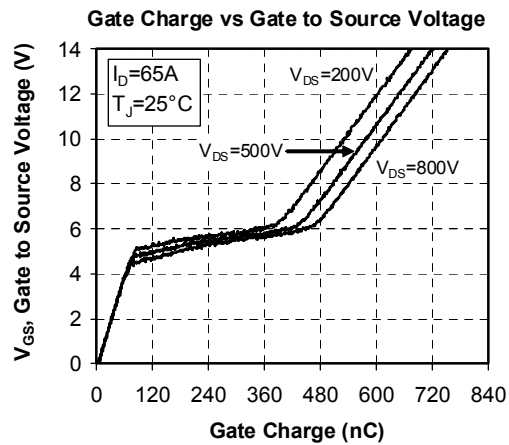
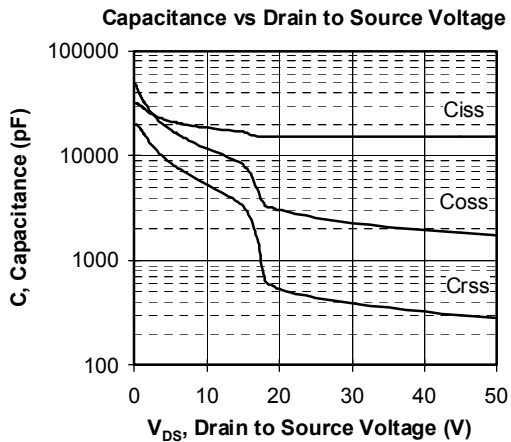
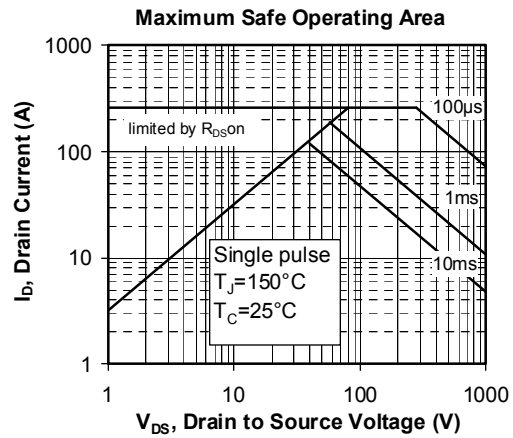
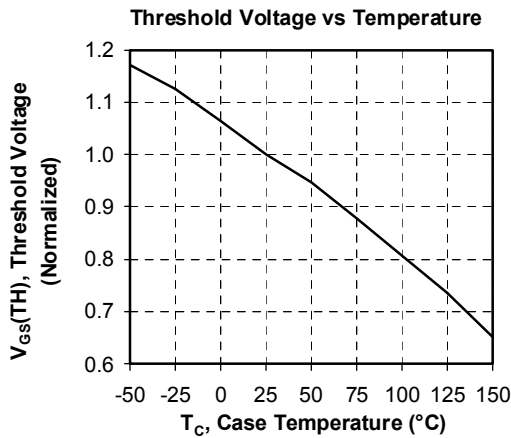
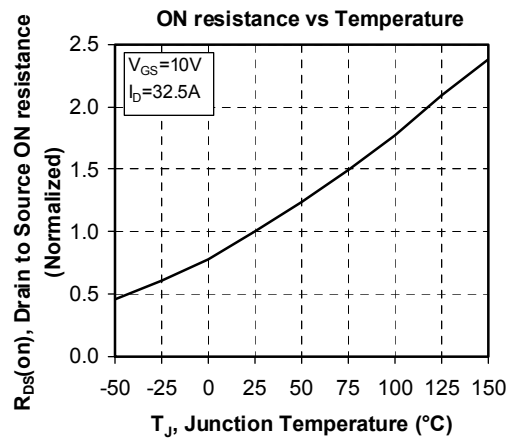
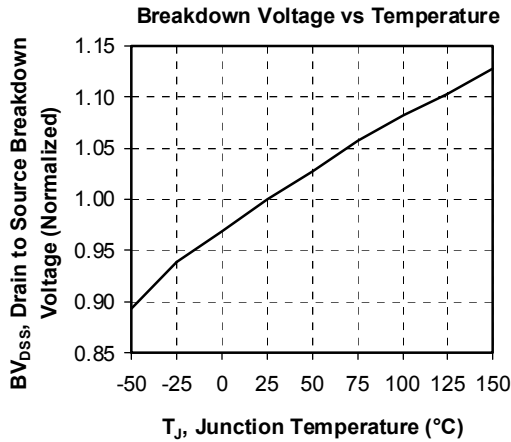
Thermal and package characteristics

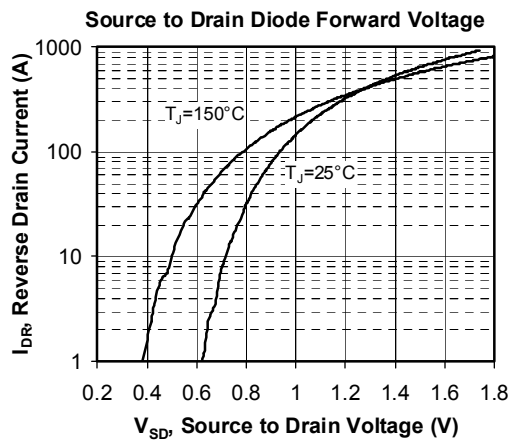
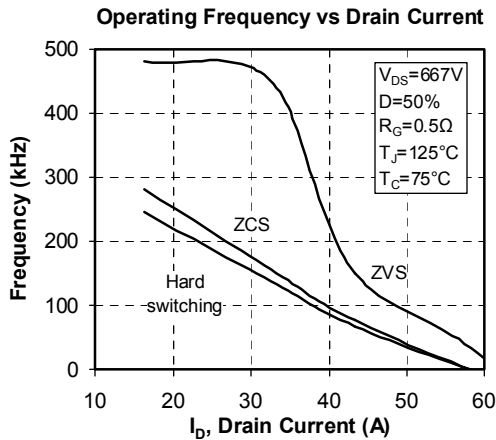
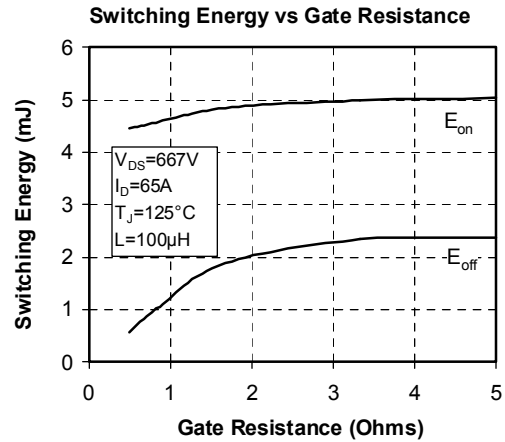
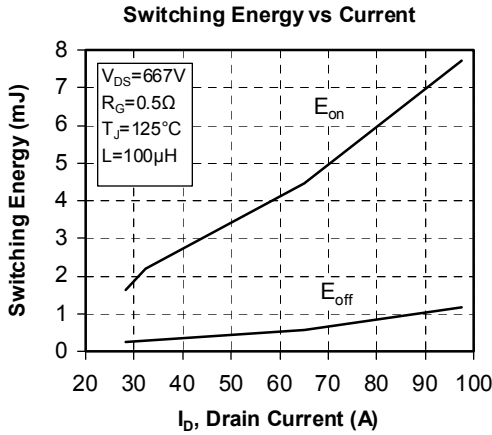
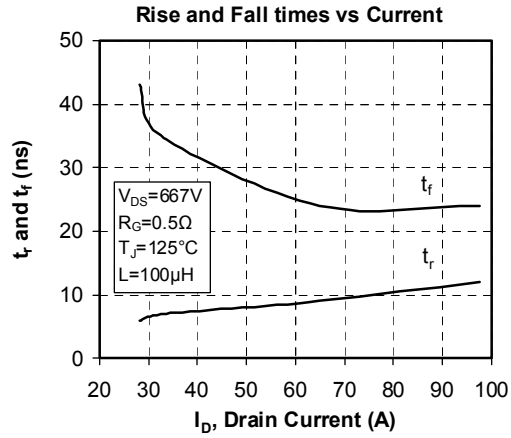
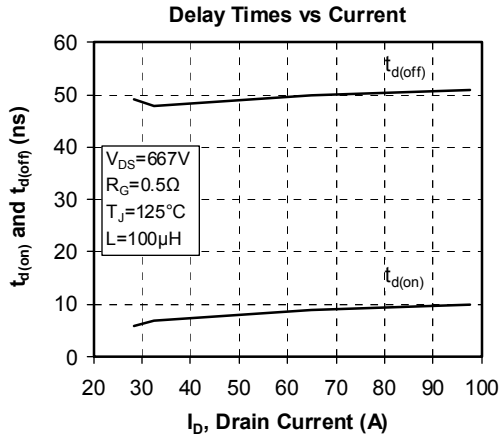
Symbol	Characteristic	Min	Typ	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance	Transistor		0.10	$^\circ C/W$	
		Diode series		0.65		
		Diode parallel		0.46		
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t=1$ min, $I_{isol}<1mA$, 50/60Hz	2500			V	
T_J	Operating junction temperature range	-40		150	$^\circ C$	
T_{STG}	Storage Temperature Range	-40		125		
T_C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight			280	g	

SP6 Package outline (dimensions in mm)

 See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

Typical Performance Curve







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